

Isc N-Channel MOSFET Transistor

TK31A60W, ITK31A60W

FEATURES

- Low drain-source on-resistance: $R_{DS(ON)} = 0.073\Omega$ (typ.)
- Easy to control Gate switching
- Enhancement mode: $V_{th} = 2.7$ to $3.7V$ ($V_{DS} = 10V$, $I_D = 1.5mA$)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRIPTION

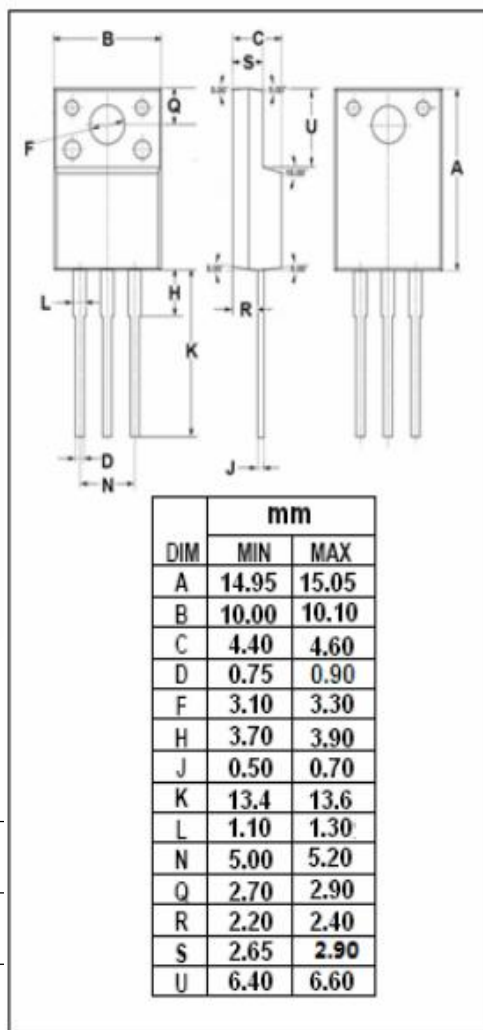
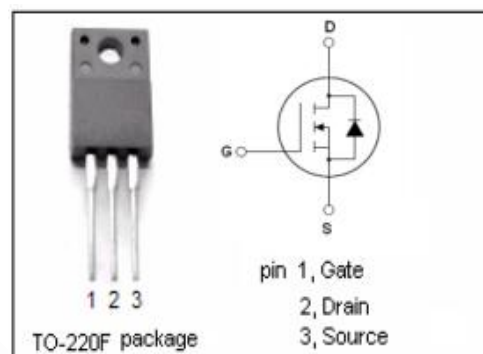
- Switching Voltage Regulators

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-Continuous	30.8	A
I_{DM}	Drain Current-Single Pulsed	123	A
P_D	Total Dissipation @ $T_c = 25^\circ C$	45	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-55~150	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	2.78	$^\circ C/W$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	62.5	$^\circ C/W$



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ELECTRICAL CHARACTERISTICS

$T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V; I_D=10mA$	600			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=10V; I_D=1.5mA$	2.7		3.7	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V; I_D=15.4A$		73	88	$m\Omega$
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 30V; V_{DS}=0V$			± 1	μA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=600V; V_{GS}=0V$			10	μA
V_{SDF}	Diode forward voltage	$I_{DR}=30.8A, V_{GS}=0V$			1.7	V